

ABSTRACT

A semiconductor device that can be miniaturized or highly integrated is provided. The semiconductor device includes a first conductor, a metal oxide over the first conductor, a second conductor over the metal oxide, a first insulator, a second insulator over the first insulator, and a
5 third conductor over the second insulator. The first conductor includes a region overlapping with the metal oxide. The metal oxide has a first opening. The second conductor has a second opening. The first opening and the second opening overlap with each other. The first insulator is placed on the inner side of each of the first opening and the second opening. The second insulator is placed in a depressed portion of the first insulator. The third conductor is placed in a
10 depressed portion of the second insulator.

(Fig.5B)